



### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### **Features**

- Low On-Resistance
  - $60 \text{ m}\Omega$  @  $V_{GS} = 4.5V$
  - 80 m $\Omega$  @  $V_{GS} = 2.5V$
  - 130 m $\Omega$  @  $V_{GS}$  = 1.5V
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- **ESD Protected Gate**
- Fast Switching Speed
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

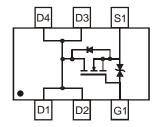
- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.015 grams (approximate)

SOT-26





Top View



Top View Internal Schematic

# Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	±8	V
Drain Current (Note 1)	I <sub>D</sub>	3.2	А
Pulsed Drain Current (Note 1)	I <sub>DM</sub>	12.8	A

# Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_{D}$	900	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	139	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

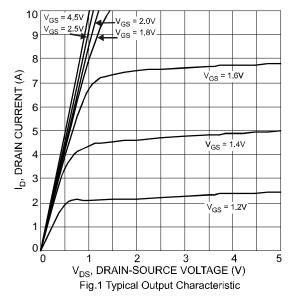
## Electrical Characteristics @TA = 25°C unless otherwise specified

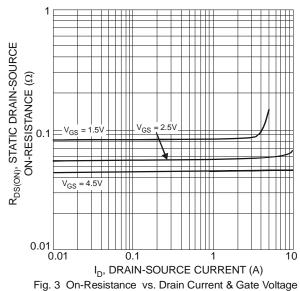
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)		•					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 100 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±5	μА	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	_	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		) —	40 50 76	60 80 130	$m\Omega$	$V_{GS} = 4.5V, I_D = 6A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>					$V_{GS} = 2.5V, I_D = 2A$	
						$V_{GS} = 1.5V, I_D = 1.0A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	8	_	S	V <sub>DS</sub> =10V, I <sub>D</sub> = 6A	
Diode Forward Voltage (Note 4)	V <sub>SD</sub>		0.7	1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2A	
DYNAMIC CHARACTERISTICS	-		-				
Input Capacitance	C <sub>iss</sub>		476	_	pF		
Output Capacitance	C <sub>oss</sub>	_	77	_	pF	$V_{DS} = 15V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	59	_	pF		

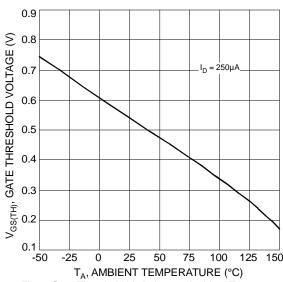
Notes:

- 1. Device mounted on FR-4 PCB, minimum recommended pad layout on 2oz. Copper pads.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- 4. Short duration pulse test used to minimize self-heating effect.

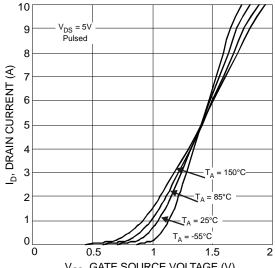












V<sub>GS</sub>, GATE SOURCE VOLTAGE (V) Fig. 2 Typical Transfer Characteristics

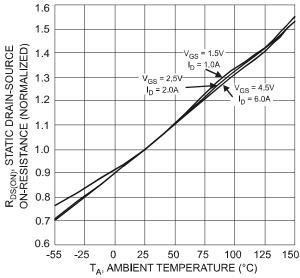
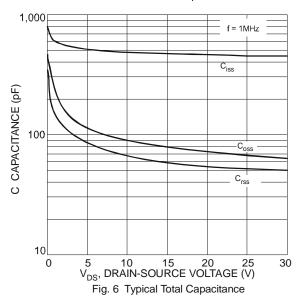


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





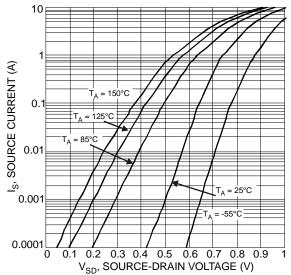


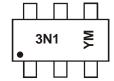
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

# **Ordering Information** (Note 5)

Part Number	Case	Packaging
DMN3115UDM-7	SOT-26	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**

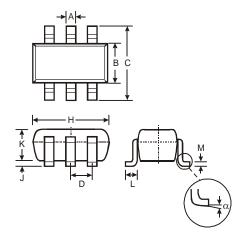


3N1 = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

Year	2007	20	800	2009	2010	20	011	2012	2013	2	014	2015
Code	J	,	V	W	X		Υ	Z	Α		В	С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

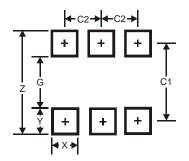
# **Package Outline Dimensions**



SOT-26						
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D		_	0.95			
Н	2.90	3.10	3.00			
J	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
α	0°	8°				
AII D	All Dimensions in mm					



## **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Υ	0.80
C1	2.40
C2	0.95

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